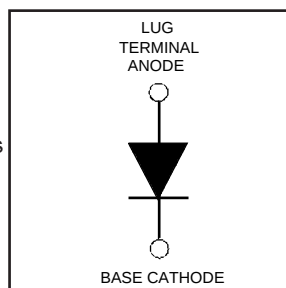


HFA180NH40

Ultrafast, Soft Recovery Diode

Features

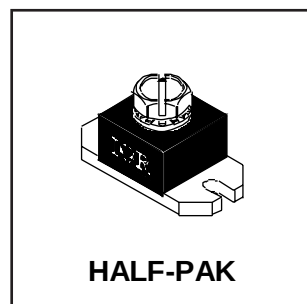
- Reduced RFI and EMI
- Reduced Snubbing
- Extensive Characterization of Recovery Parameters



$V_R = 400V$
$V_F(\text{typ.})^{\textcircled{3}} = 1.1V$
$I_{F(AV)} = 180A$
$Q_{rr}(\text{typ.}) = 420nC$
$I_{RRM}(\text{typ.}) = 8.7A$
$t_{rr}(\text{typ.}) = 45ns$
$di_{(rec)M}/dt(\text{typ.})^{\textcircled{3}} = 280A/\mu s$

Description

HEXFRED™ diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems. An extensive characterization of the recovery behavior for different values of current, temperature and di/dt simplifies the calculations of losses in the operating conditions. The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for power converters, motors drives and other applications where switching losses are significant portion of the total losses.



Absolute Maximum Ratings

	Parameter	Max.	Units
V_R	Cathode-to-Anode Voltage	400	V
$I_F @ T_C = 25^\circ C$	Continuous Forward Current	321	A
$I_F @ T_C = 100^\circ C$	Continuous Forward Current	160	
I_{FSM}	Single Pulse Forward Current ①	1200	
I_{AS}	Maximum Single Pulse Avalanche Current ②	5.0	mJ
E_{AS}	Non-Repetitive Avalanche Energy ②	1.4	
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	625	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	250	
T_J	Operating Junction and	-55 to +150	$^\circ C$
T_{STG}	Storage Temperature Range		

Thermal - Mechanical Characteristics

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	—	0.20	$^\circ C/W$
$R_{\theta CS}$	Case-to-Sink, Flat , Greased Surface	—	0.15	—	K/W
Wt	Weight	—	26 (0.9)	—	g (oz)
	Mounting Torque	15 (1.7)	—	25 (2.8)	lbf•in
	Terminal Torque	20 (2.2)	—	40 (4.4)	(N•m)

Note: ① Limited by junction temperature
 ② L = 100μH, duty cycle limited by max T_J
 ③ 125°C

HFA180NH40

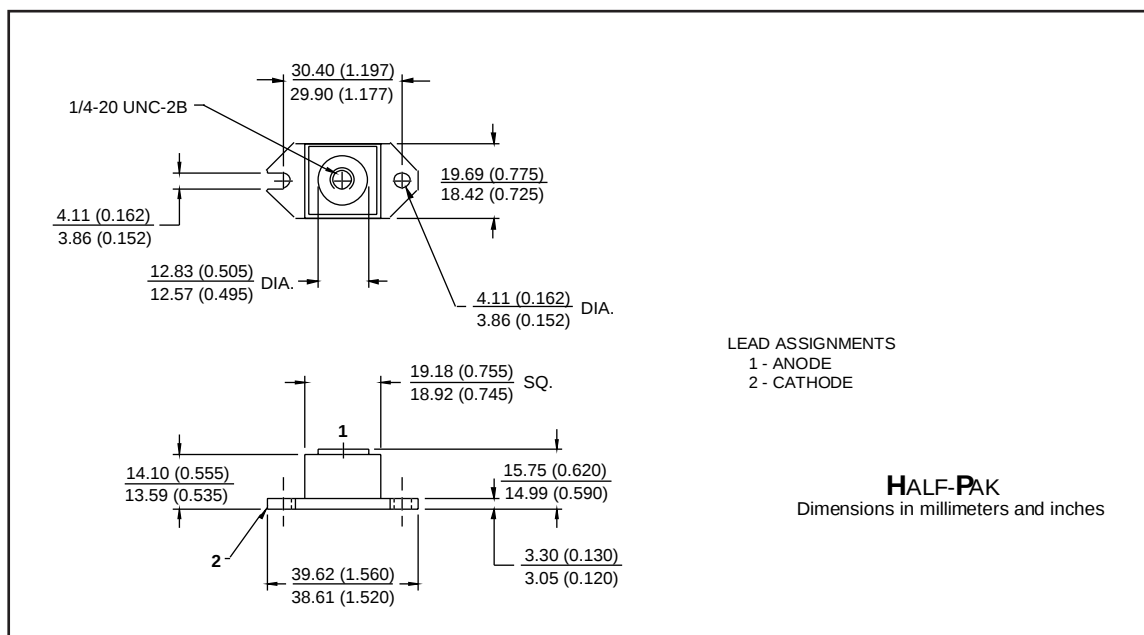
International
IOR Rectifier

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
V_{BR}	Cathode Anode Breakdown Voltage	400	—	—	V	$I_R = 100\mu\text{A}$
V_{FM}	Max Forward Voltage	—	1.10	1.35	V	$I_F = 180\text{A}$
		—	1.40	1.65		$I_F = 360\text{A}$
		—	1.10	1.30		$I_F = 180\text{A}, T_J = 125^\circ\text{C}$
I_{RM}	Max Reverse Leakage Current	—	2.0	12	μA	$V_R = V_R$ Rated
		—	3.0	16	mA	$T_J = 125^\circ\text{C}, V_R = 320\text{V}$
C_T	Junction Capacitance	—	370	500	pF	$V_R = 200\text{V}$
L_S	Series Inductance	—	5.0	—	nH	From top of terminal hole to mounting plane

Dynamic Recovery Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
t_{rr}	Reverse Recovery Time	—	45	—	ns	$I_F = 1.0\text{A}, di/dt = 200\text{A}/\mu\text{s}, V_R = 30\text{V}$
t_{rr1}		—	90	140		$T_J = 25^\circ\text{C}$ See Fig.
t_{rr2}		—	290	440		$T_J = 125^\circ\text{C}$ 5
I_{RRM1}	Peak Recovery Current	—	8.7	20	A	$T_J = 25^\circ\text{C}$ See Fig.
I_{RRM2}		—	18	30		$T_J = 125^\circ\text{C}$ 6
Q_{rr1}	Reverse Recovery Charge	—	420	1100	nC	$T_J = 25^\circ\text{C}$ See Fig.
Q_{rr2}		—	2600	7000		$T_J = 125^\circ\text{C}$ 7
$di_{(rec)M}/dt1$	Peak Rate of Fall of Recovery Current	—	300	—	$\text{A}/\mu\text{s}$	$T_J = 25^\circ\text{C}$ See Fig.
$di_{(rec)M}/dt2$	During t_b	—	280	—		$T_J = 125^\circ\text{C}$ 8



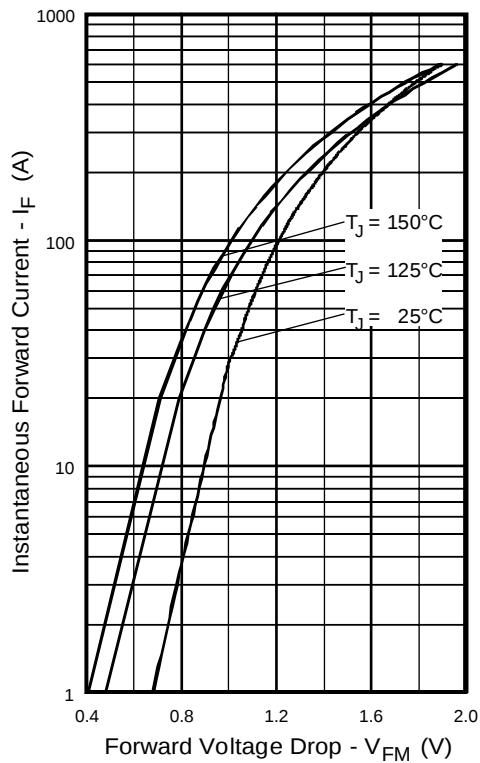


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

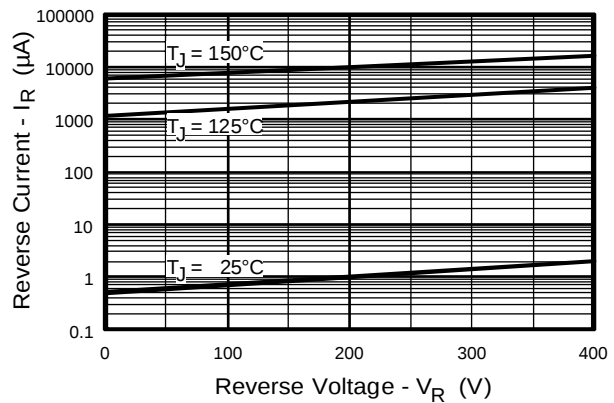


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

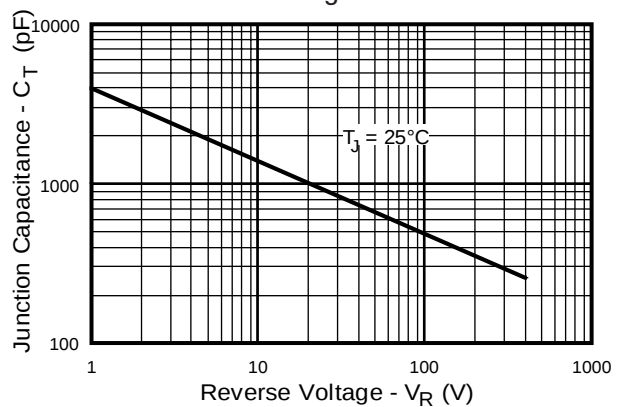


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

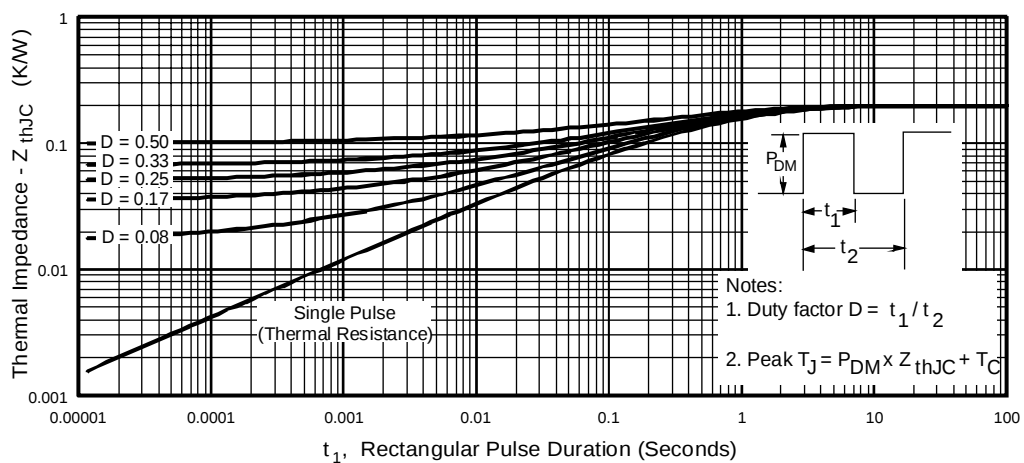


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

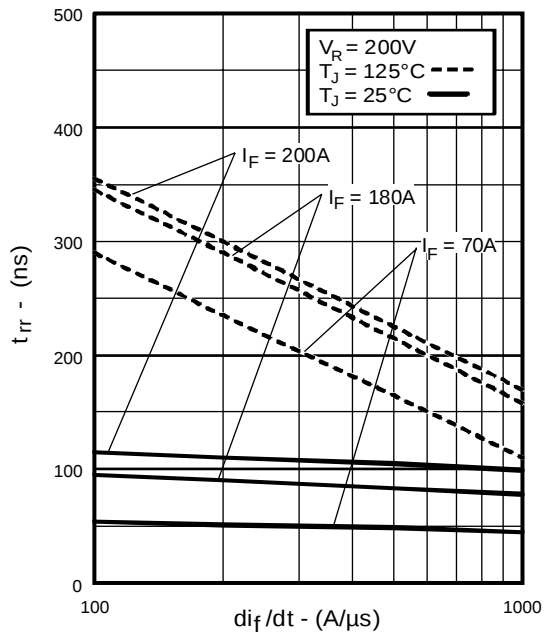


Fig. 5 - Typical Reverse Recovery vs. di_f/dt

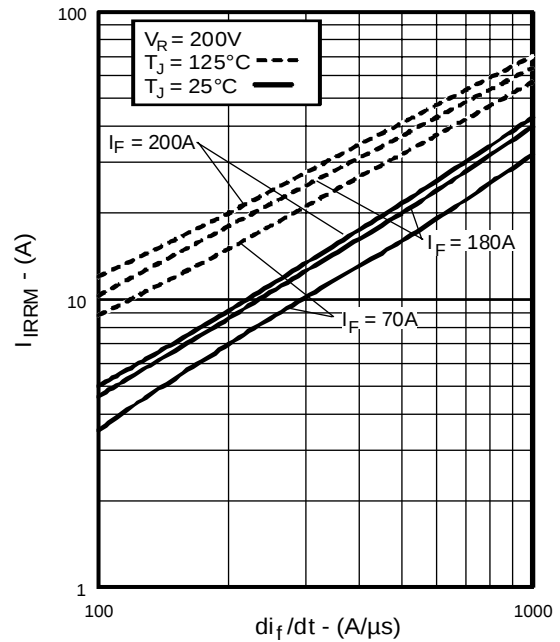


Fig. 6 - Typical Recovery Current vs. di_f/dt

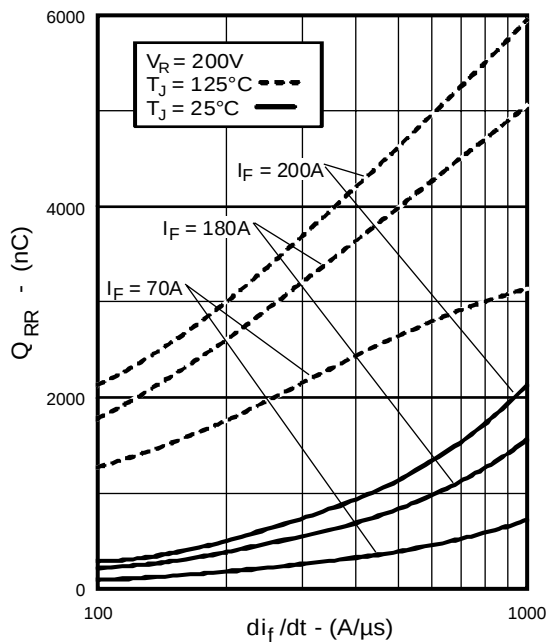


Fig. 7 - Typical Stored Charge vs. di_f/dt

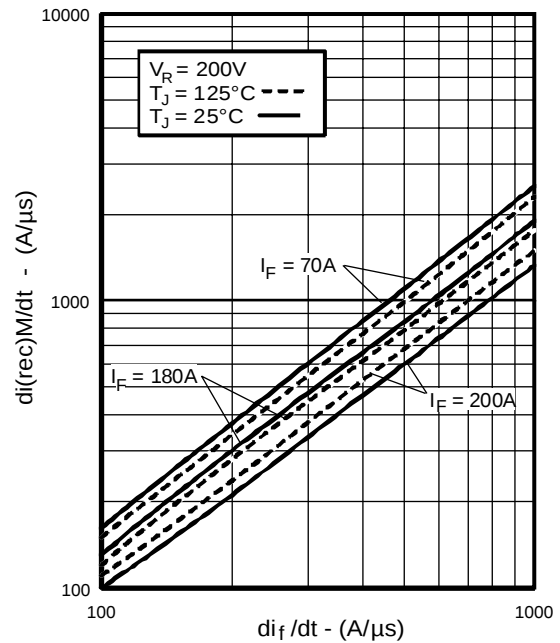


Fig. 8 - Typical $di_{(rec)M}/dt$ vs. di_f/dt

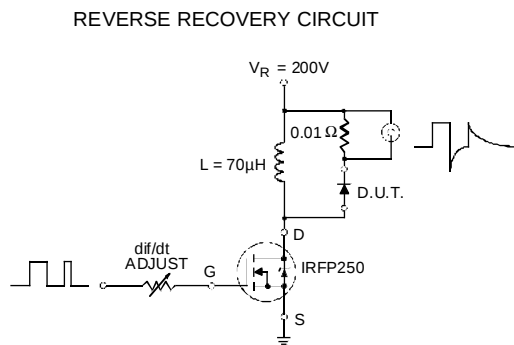


Fig. 9 - Reverse Recovery Parameter Test Circuit

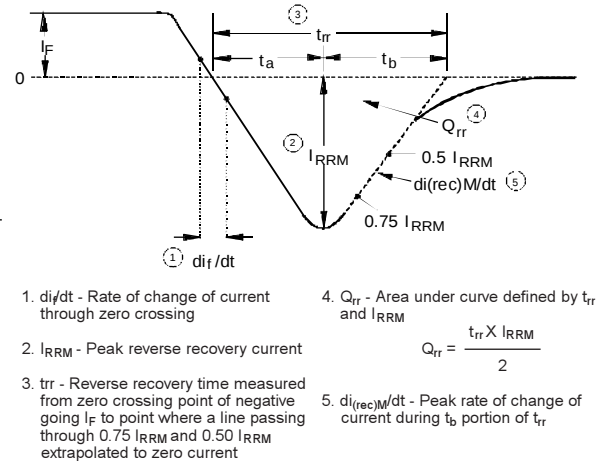


Fig. 10 - Reverse Recovery Waveform and Definitions

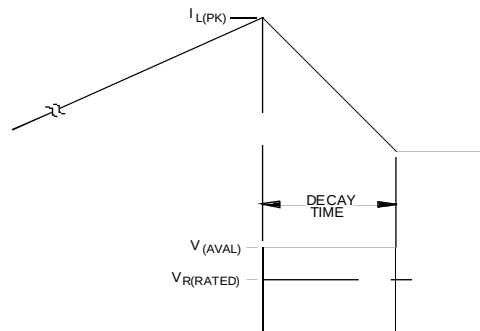
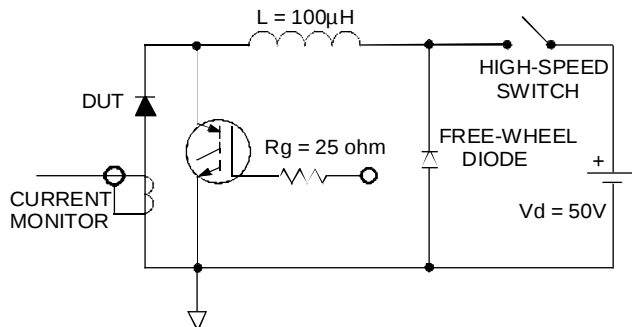


Fig. 11 - Avalanche Test Circuit and Waveforms